

Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1780		PRIORITY SERIAL NO. 09/37,645	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gursel S. Sandhu et al.		PRIORITY FILING DATE April 17, 2001	
				PRIORITY GROUP 2811			
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
JS	AA	5,520,975	6/1994	Coderbaum et al.	457	44	
JS	AB	5,534,851	8/1994	Pfanner et al.	257	67	
JS	AC	5,373,170	12/1994	Pfanner et al.	257	69	
JS	AD	5,411,909	5/1995	Manning et al.	437	52	
JS	AE	5,418,393	5/1995	Hayden	257	347	
JS	AF	4,945,065	7/31/90	Gregory, et al.	437	4	
JS	AG	5,312,108	5/18/95	Liu, et al.	437	60	
JS	AH	5,323,240	6/4/96	Zhang, et al.	437	21	
JS	AI	5,726,096	2/98	Jung	438	592	
JS	AJ	4,569,697	7/86	Tsu et al.			
JS	AK	5,665,611	9/97	Sandhu et al.	438	102	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
	AL	281054A1	7/90	Germany - Meade, et al.			Yes No
	AM						
	AP						
OTHER PRIOR ART (including Author, Title, Date, Portion(s) Pages, Etc.)							
JS	AR			Fulbeck, G.P. et al., "Hydrogen Passivation of Polysilicon MOSFET's From A Plasma Nitride Source", IEEE, 1984 pp. 408-410			
JS	AS			Karins, T.L., "Hydrogenation of Transistors Fabricated in Polycrystalline-Silicon Films", IEEE, 1980, pp. 159-161			
JS	AT			Seger, C.H. et al., "Studies of the hydrogen passivation of silicon grain boundaries", J. Appl. Phys. 52, February 1981, pp. 1030-1033			
EXAMINER				DATE CONSIDERED			
hanna Schetty				10/25/04			
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							

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LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Genej S. Sandhu et al.		PRIORITY FILING DATE April 17, 2001	
				PRIORITY GROUP 2813			
U.S. PATENT DOCUMENTS							
*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
LL	AA	5,605,848	2/97	Ngocarm			
LL	AB	5,364,803	11/93	Lay et al.			
LL	AC	5,830,302	11/98	Yang et al.	428	592	
LL	AD	5,372,660	12/94	Fellner et al.	427	578	
LL	AE	5,352,332	9/98	Yang et al.			
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FOREIGN PATENT DOCUMENTS							
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							Yes No
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	AP						
OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)							
LL	AR			Kitajima, H. et al. "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstracts - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176			
LL	AS			Sénada, Takashi et al. "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 724, Accepted for Publication 1990			
EXAMINER		hans schult		DATE CONSIDERED		10/25/04	
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Form PTO-1449		U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE		ATTY. DOCKET NO. M122-1730		SERIAL NO. 09/902,177	
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)				APPLICANT Gurtej S. Sandhu et al.		PRIORITY GROUP 2813	
FILING DATE July 9, 2001				PRIORITY GROUP 2813			

  

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Examiner Initial	Class	Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
   	AA	3,733,343	5/19/93	Sandhu et al.	438	163	
	AB	6,001,675	12/14/99	Sandhu et al.	438	151	
	AC	6,077,732	6/20/00	Sandhu et al.	438	153	
	AD	6,238,957	5/29/01	Sandhu et al.	438	151	
	AE						
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	AA	5,605,848	2/97	Ngaoaram			
	AB	5,364,803	11/94	Lur et al.			
	AC	5,830,802	11/98	Tseng et al.	438	592	
	AD	5,372,860	12/94	Fehlner et al.	427	578	
	AE	5,552,332	9/96	Tseng et al.			
	AF	5,753,543	5/19/98	Sandhu et al.	438	163	
	AG	6,001,675	12/14/99	Sandhu et al.	438	151	
	AH	6,077,732	6/20/00	Sandhu et al.	438	158	
	AI	6,238,957	5/29/01	Sandhu et al.	438	151	
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## FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Subclass	Translation	
							Yes	No
	AL							
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	AN							
	AO							
	AP							

## OTHER PRIOR ART (including Author, Title, Date, Pertinent Pages, Etc.)

	AR		Kitajima, H. et al., "Leakage Current Reduction in Sub-Micron Channel Poly-Si TFTs", Extended Abstract - 1991 International Conference on Solid State Devices and Materials, Yokohama, 1991, pp. 174-176					
	AS		Sunada, Takeshi et al., "The Role of Fluorine Termination in the Chemical Stability of HF-Treated Si Surfaces", Dept. of Electrical Engineering, Hiroshima University, Higashi-Hiroshima 734. Accepted for Publication 1990					

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